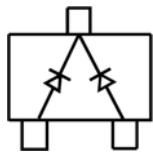


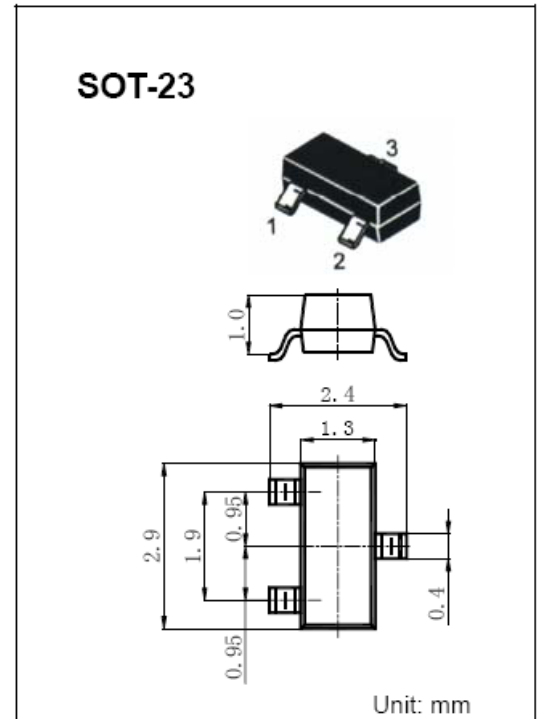
Switching Diode

FEATURES

- Power dissipation, P_D : 225 mW ($T_A=25^\circ\text{C}$)
- Forward Current, I_F : 200 mA
- Reverse Voltage, V_R : 50 V
- Operating and storage junction temperature range: T_J, T_{stg} : -55°C to $+150^\circ\text{C}$
- SOT-23 Plastic-Encapsulate package



Device Making: JA



ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=5\mu\text{A}$	50		V
Reverse voltage leakage current	I_R	$V_R=50\text{V}$		0.1	μA
Forward voltage	V_F	$I_F=100\text{mA}$		1	V
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$		2	pF
Reverse recovery time	t_{rr}			4	ns

Note: Unless otherwise specified, these specifications apply over the operating ambient temperature of 25°C .

Disclaimer

Information furnished by Silicon Standard Corporation is believed to be accurate and reliable. However, Silicon Standard Corporation makes no guarantee or warranty, expressed or implied, as to the reliability, accuracy, timeliness or completeness of such information and assumes no responsibility for its use, or for infringement of any patent or other intellectual property rights of third parties that may result from its use. Silicon Standard reserves the right to make changes as it deems necessary to any products described herein for any reason, including without limitation enhancement in reliability, functionality or design. No license is granted, whether expressly or by implication, in relation to the use of any products described herein or to the use of any information provided herein, under any patent or other intellectual property rights of Silicon Standard Corporation or any third parties.